NSN 5961-00-163-3513

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Inclosure Material:
Ceramic and metal
Overall Length:
Between 0.790 inches and 0.810 inches
Overall Height:
Between 0.145 inches and 0.185 inches
Overall Width:
Between 0.740 inches and 0.760 inches
Mounting Facility Quantity:
2
Internal Configuration:
Junction contact
Mounting Method:
Unthreaded hole
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
50.0 breakdown voltage, collector-to-base, emitter open and 50.0 breakdown voltage, collector-to-emitter, with specified resistance
between base and emitter and 3.5 breakdown voltage, emitter-to-base, collector open
Current Rating Per Characteristic:
4.00 amperes source cutoff current and 500.00 microamperes zero-gate-voltage source current preset
Power Rating Per Characteristic:
20.0 watts forward power dissipation, dc universal and 50.0 watts forward power dissipation, dc pascal
Transfer Ratio:
20.0 static forward current transfer ratio, common-emitter and 120.0 static forward current transfer ratio, common-emitter
Maximum Operating Tempurature Per Measurement Point:
200.0 degrees celsius junction
Special Features:
Junction pattern arrangement: npn
Test Data Document:
67177-47g3220 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.
excludes any specification, standard or other document that may be referenced in a basic governing drawing)
Terminal Type And Quantity:
2 ribbon and 1 case
Shelf Life:
N/a
Unit Of Measure:
Demilitarization:
No
Fiig: